



CHENMKO ENTERPRISE CO.,LTD

Lead free devices

**SURFACE MOUNT
PNP Switching Transistor**

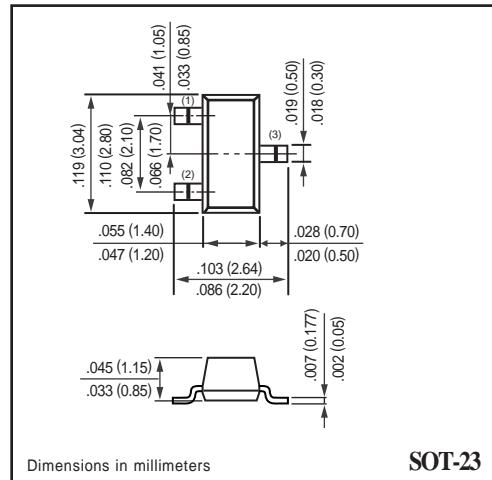
VOLTAGE 20 Volts CURRENT 3 Ampere

CHT5889PT

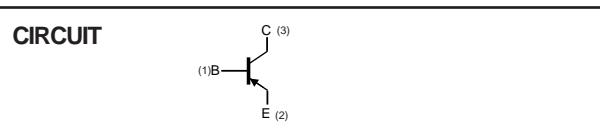
FEATURE
* Small surface mounting type. (SOT-23)
* Low Collector-Emitter saturation voltage.
CONSTRUCTION
* PNP Silicon Transistor
MARKING
* 5889



SOT-23



SOT-23



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	—	-20	V
V_{CEO}	collector-emitter voltage	open base	—	-20	V
V_{EBO}	emitter-base voltage	open collector	—	-7	V
I_c	collector current DC		—	-3.0	A
I_{CP}	collector current (Pulse)		—	-5.0	A
I_B	base current		—	-0.3	A
P_{tot}	total power dissipation	$T_{amb} \leq 25^\circ\text{C}$; note 1	—	460	mW
T_{stg}	storage temperature		-55	+150	$^\circ\text{C}$
T_j	junction temperature		—	150	$^\circ\text{C}$

2008-01

Note

- FR-4 @ 100mm^2 , 1 oz. copper traces.

RATING CHARACTERISTIC CURVES (CHT5889PT)

ELECTRICAL CHARACTERISTICS

$T_{amb} = 25^{\circ}\text{C}$ unless otherwise noted.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
BV_{CBO}	collector-base breakdown voltage	$I_E = 0; I_C = -100 \mu\text{A}$	-20	—	V
BV_{CEO}	collector-emitter breakdown voltage	$I_B = 0; I_C = -10 \text{ mA}$	-20	—	V
BV_{EBO}	emitter-base breakdown voltage	$I_C = 0; I_E = -100 \mu\text{A}$	-7	—	V
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = - 20 \text{ V}$	—	-100	nA
I_{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = - 7 \text{ V}$	—	-100	nA
h_{FE}	DC current gain	$V_{CE} = -2 \text{ V}; I_C = -500 \text{ mA}$ $V_{CE} = -2 \text{ V}; I_C = -1600 \text{ mA}$	200 100	500 —	
V_{CEsat}	collector-emitter saturation voltage	$I_C = -1600 \text{ mA}, I_B = -53 \text{ mA}$	—	-190	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = -1600 \text{ mA}, I_B = -53 \text{ mA}$	—	-1.1	V
C_c	collector capacitance	$I_E = i_e = 0; V_{CB} = -10 \text{ V}; f = 1 \text{ MHz}$	—	40 _{Typ.}	pF
f_T	transition frequency	$I_E = 500 \text{ mA}; V_{CE} = - 2 \text{ V};$	—	160 _{Typ.}	MHz

RATING CHARACTERISTIC CURVES (CHT5889PT)

Figure 1. Grounded Emitter Propagation Characteristics

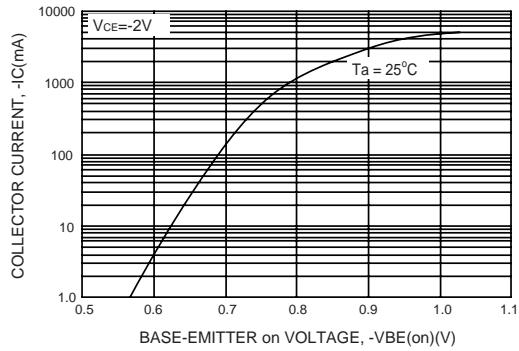


Figure 2. Collector-Emitter Saturation Voltage vs Collector Current

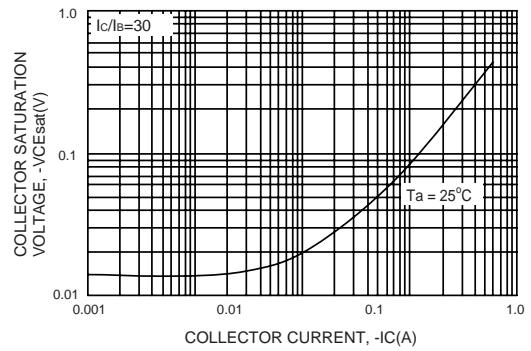


Figure 3. DC Current Gain

